

MOS FIELD EFFECT TRANSISTOR

μ PA2520

N-CHANNEL MOS FET FOR SWITCHING

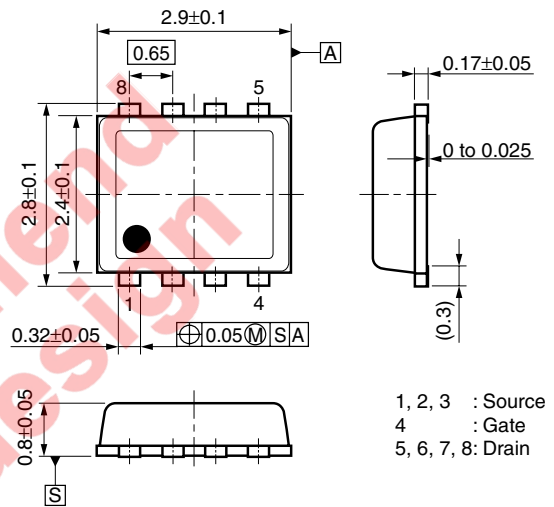
DESCRIPTION

The μ PA2520 is N-channel MOS Field Effect Transistor designed for DC/DC converter and power management applications of portable equipments.

FEATURES

- Low on-state resistance
 $R_{DS(on)1} = 13.2 \text{ m}\Omega \text{ MAX. (} V_{GS} = 10 \text{ V, } I_D = 10 \text{ A)}$
 $R_{DS(on)2} = 17 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 5.0 \text{ A)}$
- Built-in gate protection diode
- Small and surface mount package (8-pin VSOFF (2429))
- Pb-free (This product does not contain Pb in external electrode and other parts.)

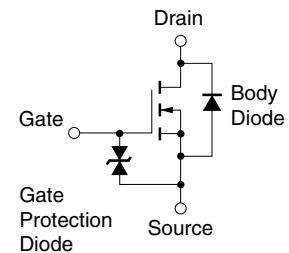
PACKAGE DRAWING (Unit: mm)



ABSOLUTE MAXIMUM RATINGS (T_A = 25°C, All terminals are connected.)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	30	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±20	V
Drain Current (DC)	I _{D(DC)}	±10	A
Drain Current (pulse) ^{Note1}	I _{D(pulse)}	±40	A
Total Power Dissipation ^{Note2}	P _{T1}	1.0	W
Total Power Dissipation (PW = 5 sec) ^{Note2}	P _{T2}	2.2	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C
Single Avalanche Current ^{Note3}	I _{AS}	10	A
Single Avalanche Energy ^{Note3}	E _{AS}	10	mJ

EQUIVALENT CIRCUIT



Notes 1. PW ≤ 10 μs, Duty Cycle ≤ 1%

2. Mounted on FR-4 board of 25.4 mm x 25.4 mm x 0.8 mm

3. Starting T_{ch} = 25°C, V_{DD} = 15 V, R_G = 25 Ω, V_{GS} = 20 → 0 V, L = 100 μH

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

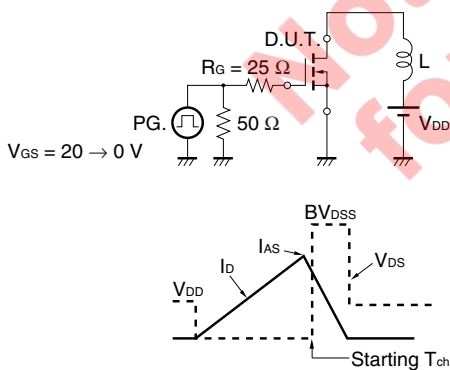
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ELECTRICAL CHARACTERISTICS (TA = 25°C, All terminals are connected.)

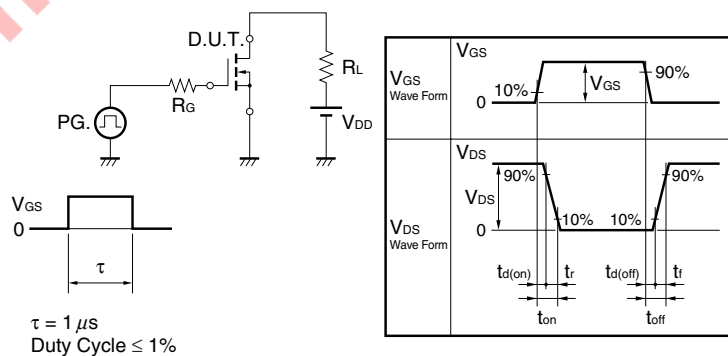
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V			10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20 V, V _{DS} = 0 V			±10	μA
Gate to Source Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5		2.5	V
Forward Transfer Admittance ^{Note}	y _{fs}	V _{DS} = 10 V, I _D = 5.0 A	4.4			S
Drain to Source On-state Resistance ^{Note}	R _{DS(on)1}	V _{GS} = 10 V, I _D = 10 A		9.4	13.2	mΩ
	R _{DS(on)2}	V _{GS} = 4.5 V, I _D = 5.0 A		12.5	17	mΩ
Input Capacitance	C _{iss}	V _{DS} = 15 V,		1100		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V,		240		pF
Reverse Transfer Capacitance	C _{rss}	f = 1 MHz		88		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V, I _D = 5.0 A,		10		ns
Rise Time	t _r	V _{GS} = 10 V,		5.5		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		40		ns
Fall Time	t _f			6.2		ns
Total Gate Charge	Q _G	V _{DD} = 15 V,		10.8		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 5 V,		3.3		nC
Gate to Drain Charge	Q _{GD}	I _D = 10 A		3.6		nC
Body Diode Forward Voltage ^{Note}	V _{F(S-D)}	I _F = 10 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	t _{rr}	I _F = 10 A, V _{GS} = 0 V,		26		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 100 A/μs		19		nC
Gate Resistance	R _G	f = 1 MHz		1.6		Ω

Note Pulsed

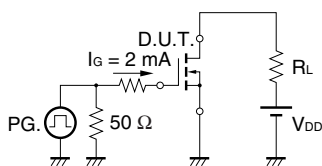
TEST CIRCUIT 1 AVALANCHE CAPABILITY



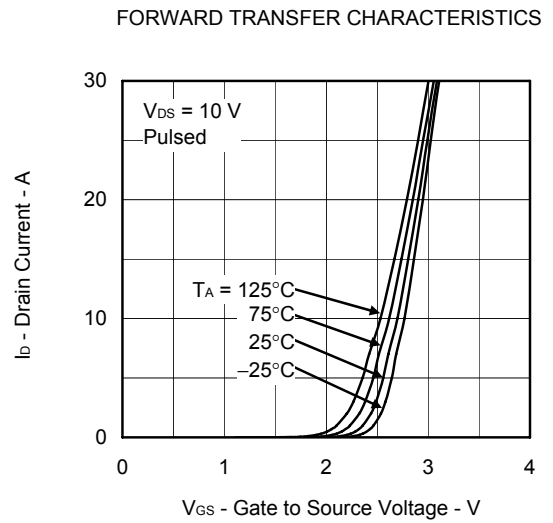
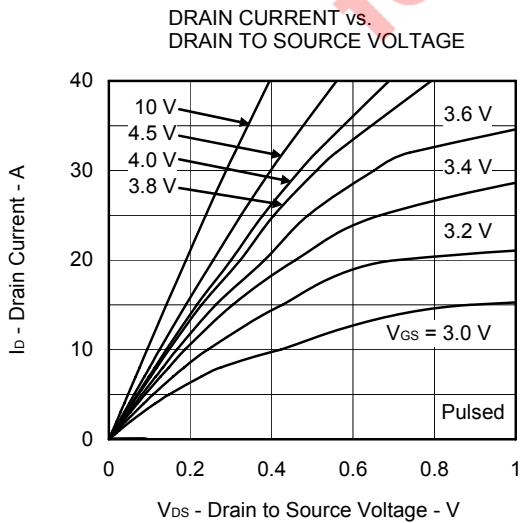
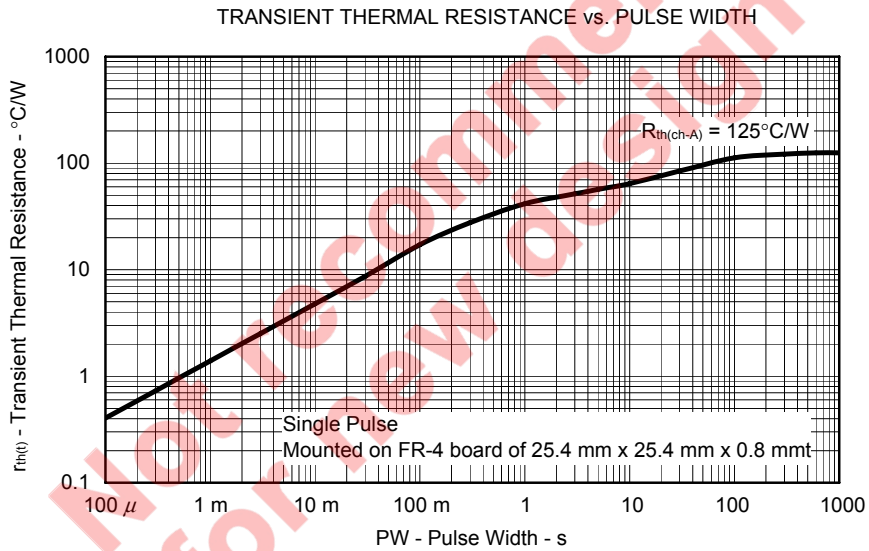
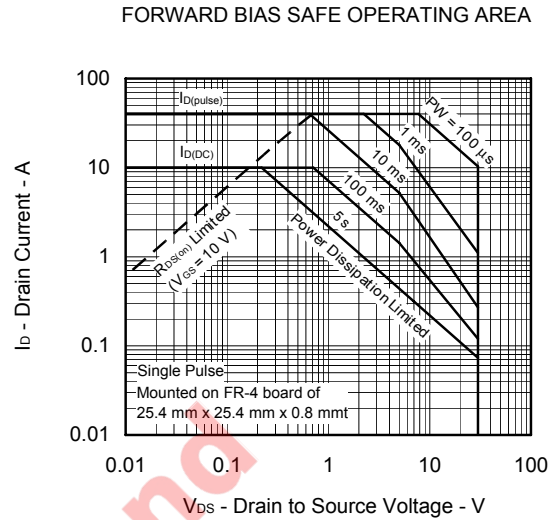
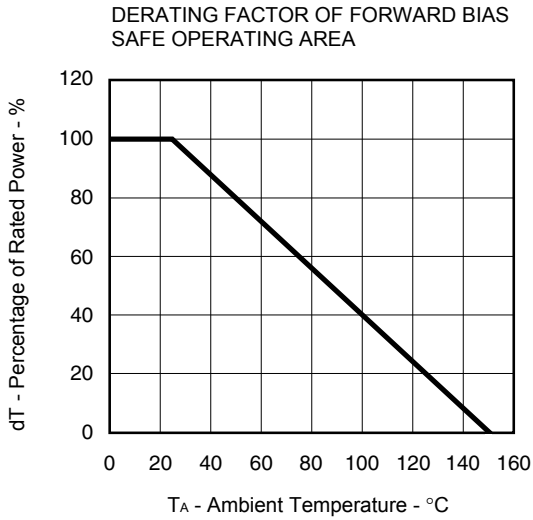
TEST CIRCUIT 2 SWITCHING TIME



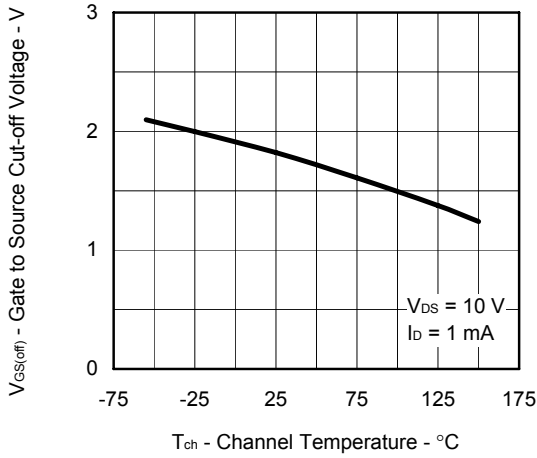
TEST CIRCUIT 3 GATE CHARGE



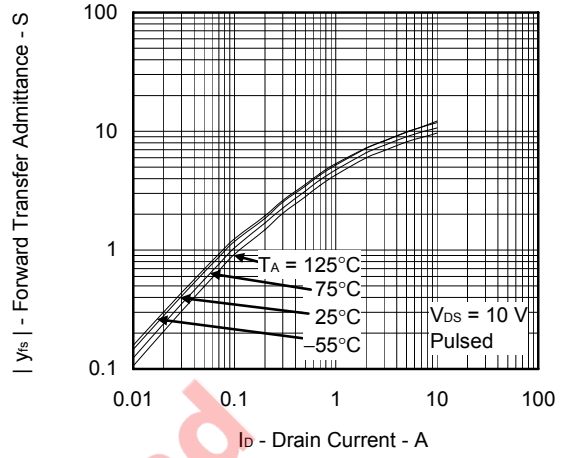
TYPICAL CHARACTERISTICS (T_A = 25°C)



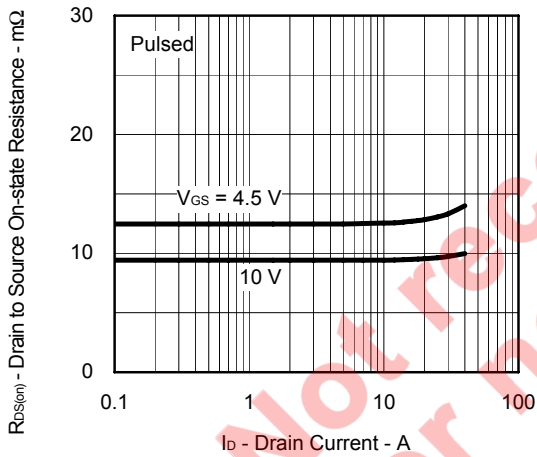
GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



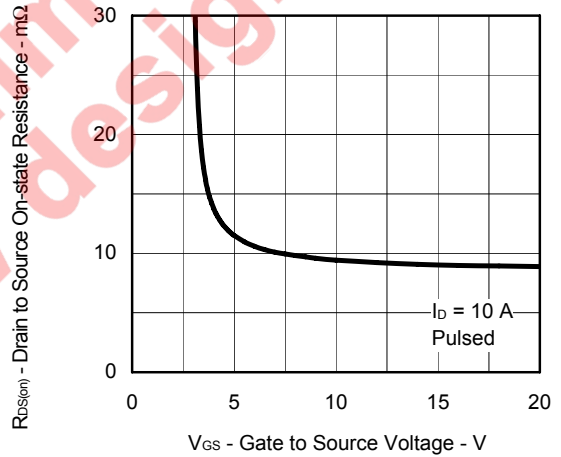
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



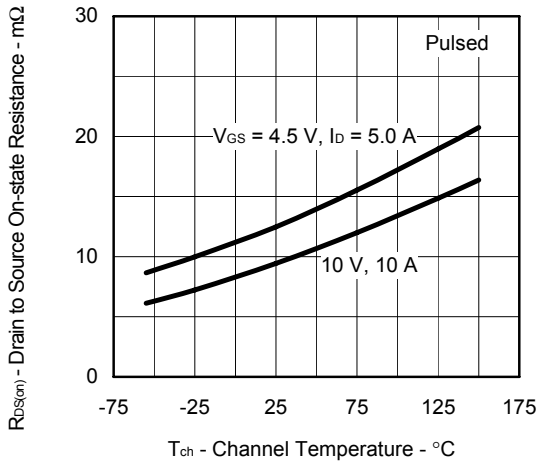
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



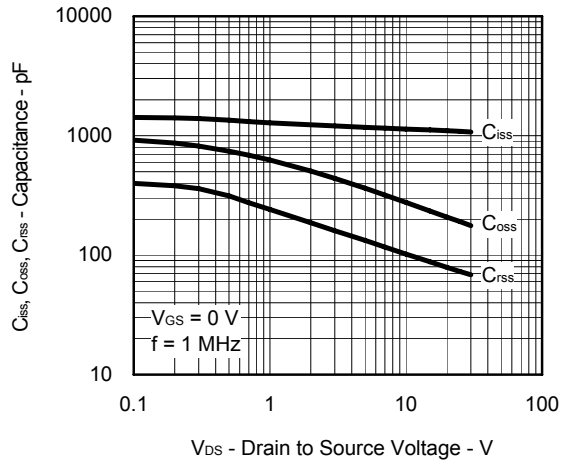
DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



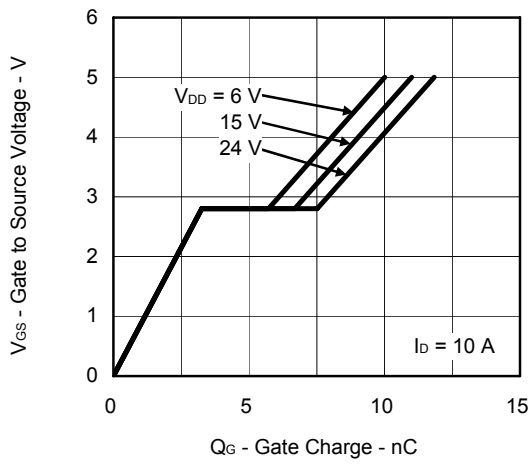
DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



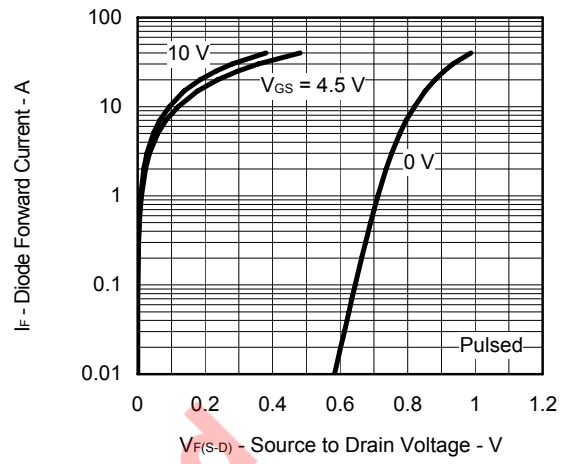
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



ORDERING INFORMATION

PART NUMBER	LEAD PLATING	PACKING	PACKAGE
μ PA2520T1H-T1-AT ^{Note}	Pure Sn	8 mm embossed taping	8-pin VSOF (2429)
μ PA2520T1H-T2-AT ^{Note}		3000 p/reel	

Note Pb-free (This product does not contain Pb in external electrode and other parts.)

Not recommended for new design